

SN74LVC2G02 デュアル 2 入力の正論理 NOR ゲート

1 特長

- テキサス・インスツルメンツの NanoFree™ パッケージで供給
- 5V V_{CC} 動作をサポート
- 5.5V までの入力電圧に対応
- 最大 t_{pd} : 4.9ns (3.3V 時)
- 低消費電力、最大 I_{CC} : 10 μ A
- 3.3V において ± 24 mA の出力駆動能力
- 標準 V_{OLP} (出力グランド・バウンス) < 0.8V ($V_{CC} = 3.3$ V, $T_A = 25^\circ$ C)
- 標準 V_{OHV} (出力 V_{OH} アンダーシュート) > 2V ($V_{CC} = 3.3$ V, $T_A = 25^\circ$ C)
- I_{off} により部分的パワーダウン・モードでの動作をサポート
- JEDEC 78、Class II 準拠で 100mA 超のラッチアップ性能
- JEDEC 22 を超える ESD 保護
 - 2000V、人体モデル (A114-A)
 - 1000V、デバイス帯電モデル (C101)

2 アプリケーション

- AV レシーバ
- オーディオ・ドック：ポータブル
- ブルーレイ・プレーヤおよびホーム・シアター
- 組み込み PC
- MP3 プレーヤおよびレコーダ (携帯用オーディオ)
- パーソナル・デジタル・アシスタント (PDA)
- 電源：テレコム/サーバーの AC/DC 電源：シングル・コントローラ：アナログおよびデジタル
- ソリッド・ステート・ドライブ (SSD)：クライアントおよびエンタープライズ
- テレビ：LCD、デジタル、高解像度 (HD)
- タブレット：エンタープライズ
- ビデオ・アナリティクス：サーバー
- ワイヤレス・ヘッドセット、キーボード、マウス

3 概要

このデュアル 2 入力の正論理 NOR ゲートは、1.65V～5.5V の V_{CC} で動作するように設計されています。

SN74LVC2G02 デバイスは、ブール関数 $Y = \overline{A + B}$ または $Y = \overline{A} \times \overline{B}$ を正論理で実行します。

ダイをパッケージとして使用する NanoFree™ パッケージ技術は、IC パッケージの概念を大きく覆すものです。

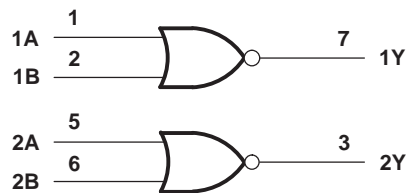
このデバイスは、 I_{off} を使用する部分的パワーダウン・アプリケーション用に完全に動作が規定されています。 I_{off} 回路が出力をディセーブルにするため、電源切断時にデバイスに電流が逆流して損傷に至ることを回避できます。

製品情報⁽¹⁾

型番	パッケージ	本体サイズ(公称)
SN74LVC2G02DCT	SSOP (8)	2.95mm × 2.8mm
SN74LVC2G02DCU	VSSOP (8)	2.3mm × 2.0mm
SN74LVC2G02YZP	DSBGA (8)	1.91mm × 0.91mm

(1) 提供されているすべてのパッケージについては、巻末の注文情報を参照してください。

概略回路図



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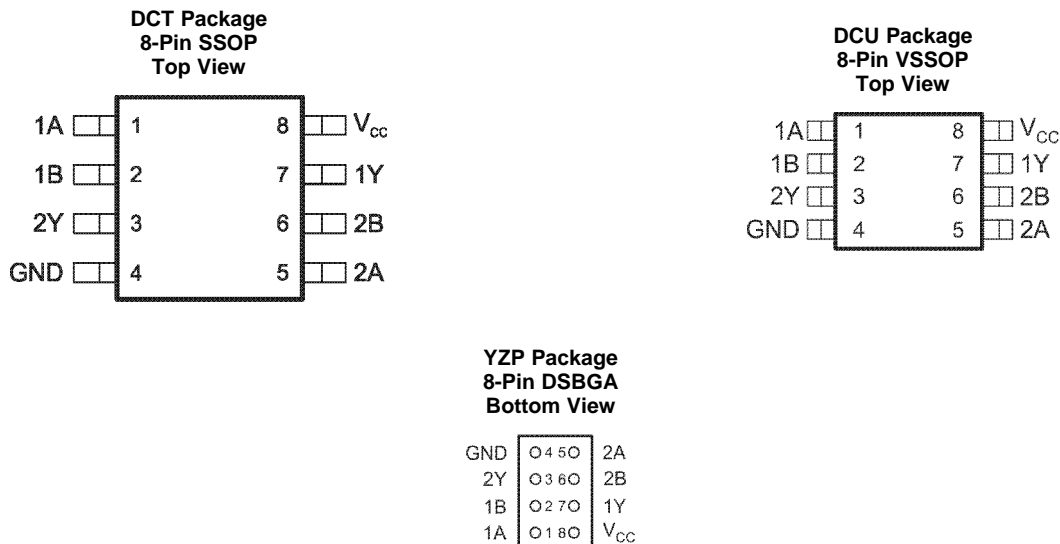
4 改訂履歴

資料番号末尾の英字は改訂を表しています。その改訂履歴は英語版に準じています。

Revision M (November 2013) から Revision N に変更	Page
• ドキュメントを新しい TI データシートのフォーマットに更新	1
• 「製品情報」表 追加	1
• Added $T_J(\text{Max})$ spec to Abs Max Ratings table	4
• Moved T_{stg} spec to Abs Max Ratings table.	4

Revision L (April 1999) から Revision M に変更	Page
• 「注文情報」表を削除	1
• Updated operating temperature range.	5

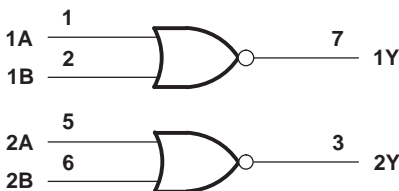
5 Pin Configuration and Functions



Pin Functions

PIN		I/O	DESCRIPTION
NAME	NO.		
1A	1	Input	Channel 1 input A
1B	2	Input	Channel 1 input B
2Y	3	Output	Channel 2 output Y
GND	4	–	Ground
2A	5	Input	Channel 2 input A
2B	6	Input	Channel 2 input B
1Y	7	Output	Channel 1 output Y
VCC	8	–	Positive supply

Logic Diagram (Positive Logic)



6 Specifications

6.1 Absolute Maximum Ratings⁽¹⁾

over operating free-air temperature range (unless otherwise noted)

		MIN	MAX	UNIT	
V_{CC}	Supply voltage range	-0.5	6.5	V	
V_I	Input voltage range ⁽²⁾	-0.5	6.5	V	
V_O	Voltage range applied to any output in the high-impedance or power-off state ⁽²⁾	-0.5	6.5	V	
V_O	Voltage range applied to any output in the high or low state ⁽²⁾⁽³⁾	-0.5	$V_{CC} + 0.5$	V	
I_{IK}	Input clamp current	$V_I < 0$	-50	mA	
I_{OK}	Output clamp current	$V_O < 0$	-50	mA	
I_O	Continuous output current		± 50	mA	
	Continuous current through V_{CC} or GND		± 100	mA	
T_J	Junction temperature		150	°C	
T_{stg}	Storage temperature		-65	150	°C

- (1) Stresses beyond those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under *Recommended Operating Conditions* is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
- (2) The input negative-voltage and output voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
- (3) The value of V_{CC} is provided in the *Recommended Operating Conditions* table.

6.2 ESD Ratings

		VALUE	UNIT
$V_{(ESD)}$	Electrostatic discharge	Human-body model (HBM), per ANSI/ESDA/JEDEC JS-001 ⁽¹⁾	± 2500
		Charged-device model (CDM), per JEDEC specification JESD22-C101 ⁽²⁾	± 1500

- (1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.
- (2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

6.3 Recommended Operating Conditions⁽¹⁾

			MIN	MAX	UNIT
V _{CC}	Supply voltage	Operating	1.65	5.5	V
		Data retention only	1.5		
V _{IH}	High-level input voltage	V _{CC} = 1.65 V to 1.95 V	0.65 × V _{CC}		V
		V _{CC} = 2.3 V to 2.7 V	1.7		
		V _{CC} = 3 V to 3.6 V	2		
		V _{CC} = 4.5 V to 5.5 V	0.7 × V _{CC}		
V _{IL}	Low-level input voltage	V _{CC} = 1.65 V to 1.95 V		0.35 × V _{CC}	V
		V _{CC} = 2.3 V to 2.7 V		0.7	
		V _{CC} = 3 V to 3.6 V		0.8	
		V _{CC} = 4.5 V to 5.5 V		0.3 × V _{CC}	
V _I	Input voltage		0	5.5	V
V _O	Output voltage		0	V _{CC}	V
I _{OH}	High-level output current	V _{CC} = 1.65 V		–4	mA
		V _{CC} = 2.3 V		–8	
		V _{CC} = 3 V		–16	
		V _{CC} = 4.5 V		–24	
I _{OL}	Low-level output current	V _{CC} = 1.65 V		4	mA
		V _{CC} = 2.3 V		8	
		V _{CC} = 3 V		16	
		V _{CC} = 4.5 V		24	
Δt/Δv	Input transition rise or fall rate	V _{CC} = 1.8 V ± 0.15 V, 2.5 V ± 0.2 V		20	ns/V
		V _{CC} = 3.3 V ± 0.3 V		10	
		V _{CC} = 5 V ± 0.5 V		5	
T _A	Operating free-air temperature		–40	125	°C

(1) All unused inputs of the device must be held at V_{CC} or GND to ensure proper device operation. Refer to the TI application report, *Implications of Slow or Floating CMOS Inputs*, literature number [SCBA004](#).

6.4 Thermal Information

THERMAL METRIC ⁽¹⁾		SN74LVC2G02			UNIT
		DCT (SSOP)	DCU (VSSOP)	YZP (DSBGA)	
		8 PINS	8 PINS	8 PINS	
R _{θJA}	Junction-to-ambient thermal resistance	182.8	201.8	99.9	°C/W
R _{θJC(top)}	Junction-to-case (top) thermal resistance	87.8	93.3	1.0	°C/W
R _{θJB}	Junction-to-board thermal resistance	97.9	124.0	27.8	°C/W
Ψ _{JT}	Junction-to-top characterization parameter	20.7	32.3	0.4	°C/W
Ψ _{JB}	Junction-to-board characterization parameter	96.6	123.6	27.8	°C/W
R _{θJC(bot)}	Junction-to-case (bottom) thermal resistance	N/A	N/A	N/A	°C/W

(1) For more information about traditional and new thermal metrics, see the [Semiconductor and IC package thermal metrics application report](#).

6.5 Electrical Characteristics

over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS	V _{CC}	–40°C to 85°C			–40°C to 125°C			UNIT
			MIN	TYP ⁽¹⁾	MAX	MIN	TYP ⁽¹⁾	MAX	
V _{OH}	I _{OH} = –100 μA	1.65 V to 5.5 V	V _{CC} – 0.1			V _{CC} – 0.1			V
	I _{OH} = –4 mA	1.65 V	1.2			1.2			
	I _{OH} = –8 mA	2.3 V	1.9			1.9			
	I _{OH} = –16 mA	3 V	2.4			2.4			
	I _{OH} = –24 mA		2.3			2.3			
	I _{OH} = –32 mA	4.5 V	3.8			3.8			
V _{OL}	I _{OL} = 100 μA	1.65 V to 5.5 V	0.1			0.1			V
	I _{OL} = 4 mA	1.65 V	0.45			0.45			
	I _{OL} = 8 mA	2.3 V	0.3			0.3			
	I _{OL} = 16 mA	3 V	0.4			0.4			
	I _{OL} = 24 mA		0.55			0.75			
	I _{OL} = 32 mA	4.5 V	0.55			0.75			
I _I	A or B inputs	V _I = 5.5 V or GND	0 to 5.5 V			±5			μA
I _{off}		V _I or V _O = 5.5 V	0			±10			μA
I _{CC}		V _I = 5.5 V or GND, I _O = 0	1.65 V to 5.5 V			10			μA
ΔI _{CC}		One input at V _{CC} – 0.6 V, Other inputs at V _{CC} or GND	3 V to 5.5 V			500			μA
C _i		V _I = V _{CC} or GND	3.3 V			5			pF

 (1) All typical values are at V_{CC} = 3.3 V, T_A = 25°C.

6.6 Switching Characteristics

 over recommended operating free-air temperature range (unless otherwise noted) (see [Figure 3](#))

PARAMETER	FROM (INPUT)	TO (OUTPUT)	–40°C to 85°C								UNIT
			V _{CC} = 1.8 V ± 0.15 V		V _{CC} = 2.5 V ± 0.2 V		V _{CC} = 3.3 V ± 0.3 V		V _{CC} = 5 V ± 0.5 V		
			MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
t _{pd}	A or B	Y	3.2	8.9	1	5.4	1	4.9	1	4.4	ns

6.7 Switching Characteristics

 over recommended operating free-air temperature range (unless otherwise noted) (see [Figure 3](#))

PARAMETER	FROM (INPUT)	TO (OUTPUT)	–40°C to 125°C								UNIT
			V _{CC} = 1.8 V ± 0.15 V		V _{CC} = 2.5 V ± 0.2 V		V _{CC} = 3.3 V ± 0.3 V		V _{CC} = 5 V ± 0.5 V		
			MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
t _{pd}	A or B	Y	3.2	10.9	1	6.4	1	5.9	1	5.4	ns

6.8 Operating Characteristics

 T_A = 25°C

PARAMETER	TEST CONDITIONS	V _{CC} = 1.8 V	V _{CC} = 2.5 V	V _{CC} = 3.3 V	V _{CC} = 5 V	UNIT	
		TYP	TYP	TYP	TYP		
C _{pd}	Power dissipation capacitance	f = 10 MHz	18	18	19	22	pF

6.9 Typical Characteristics

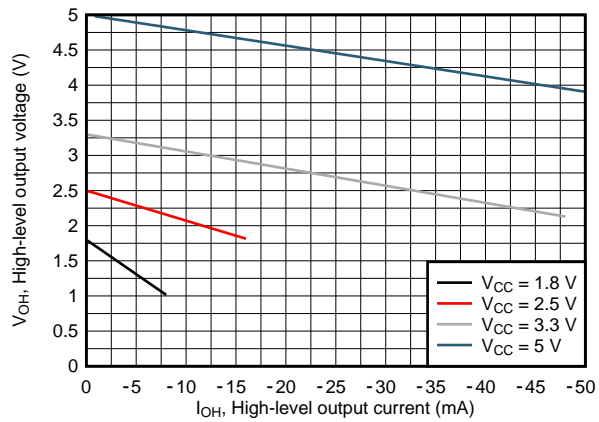


Figure 1. Simulated typical high-level output voltage (V_{OH}) across high-level output current (I_{OH}) at common supply values

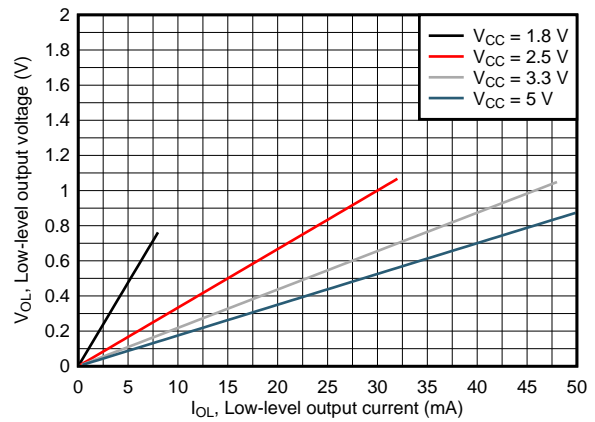
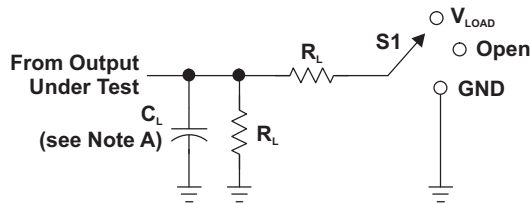


Figure 2. Simulated typical low-level output voltage (V_{OL}) across low-level output current (I_{OL}) at common supply values

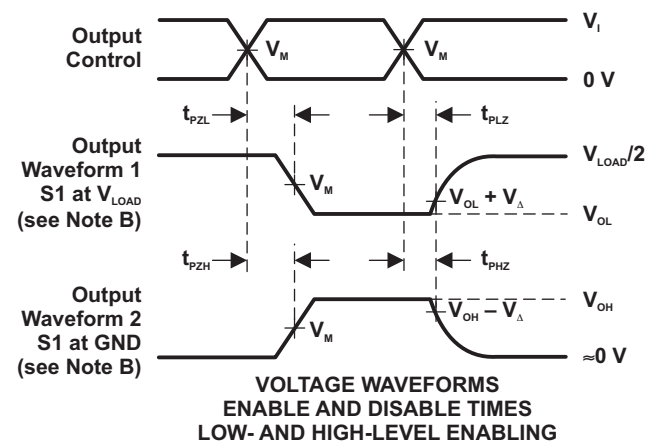
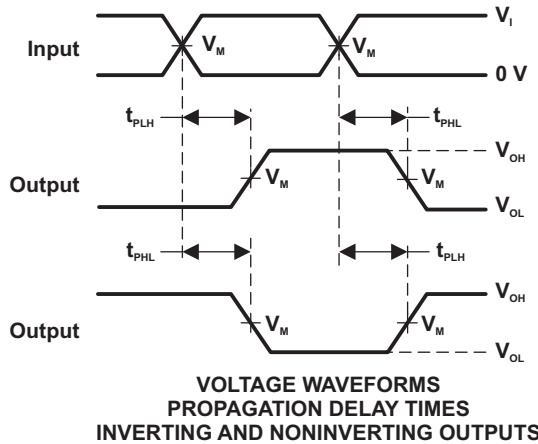
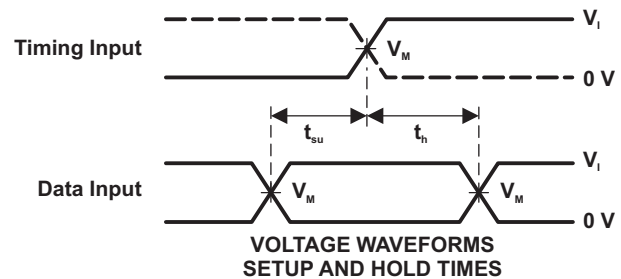
7 Parameter Measurement Information



LOAD CIRCUIT

TEST	S1
t_{PLH}/t_{PHL}	Open
t_{PLZ}/t_{PZL}	V_{LOAD}
t_{PHZ}/t_{PZH}	GND

V_{CC}	INPUTS		V_M	V_{LOAD}	C_L	R_L	V_{Δ}
	V_i	t_r/t_f					
$1.8\text{ V} \pm 0.15\text{ V}$	V_{CC}	$\leq 2\text{ ns}$	$V_{CC}/2$	$2 \times V_{CC}$	30 pF	1 k Ω	0.15 V
$2.5\text{ V} \pm 0.2\text{ V}$	V_{CC}	$\leq 2\text{ ns}$	$V_{CC}/2$	$2 \times V_{CC}$	30 pF	500 Ω	0.15 V
$3.3\text{ V} \pm 0.3\text{ V}$	3 V	$\leq 2.5\text{ ns}$	1.5 V	6 V	50 pF	500 Ω	0.3 V
$5\text{ V} \pm 0.5\text{ V}$	V_{CC}	$\leq 2.5\text{ ns}$	$V_{CC}/2$	$2 \times V_{CC}$	50 pF	500 Ω	0.3 V



- NOTES: A. C_L includes probe and jig capacitance.
 B. Waveform 1 is for an output with internal conditions such that the output is low, except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high, except when disabled by the output control.
 C. All input pulses are supplied by generators having the following characteristics: PRR \leq 10 MHz, $Z_o = 50\ \Omega$.
 D. The outputs are measured one at a time, with one transition per measurement.
 E. t_{PLZ} and t_{PHZ} are the same as t_{dis} .
 F. t_{PZL} and t_{PZH} are the same as t_{en} .
 G. t_{PLH} and t_{PHL} are the same as t_{pd} .
 H. All parameters and waveforms are not applicable to all devices.

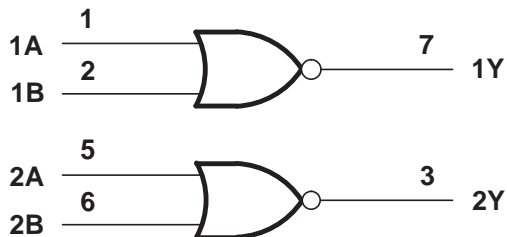
Figure 3. Load Circuit and Voltage Waveforms

8 Detailed Description

8.1 Overview

The SN74LVC2G02 device contains two 2-input positive-NOR gates and each gate performs the Boolean function $Y = A + B$ or $Y = \overline{A \cdot B}$. This device is fully specified for partial-power-down applications using I_{off} . The I_{off} circuitry disables the outputs, preventing damaging current backflow through the device when it is powered down.

8.2 Functional Block Diagram



8.3 Feature Description

- Wide operating voltage range.
 - Operates from 1.65 V to 5.5 V.
- Allows down voltage translation.
- Inputs accept voltages to 5.5 V.
- I_{off} feature allows voltages on the inputs and outputs, when V_{CC} is 0 V.

8.4 Device Functional Modes

**Table 1. Function Table
(Each Gate)**

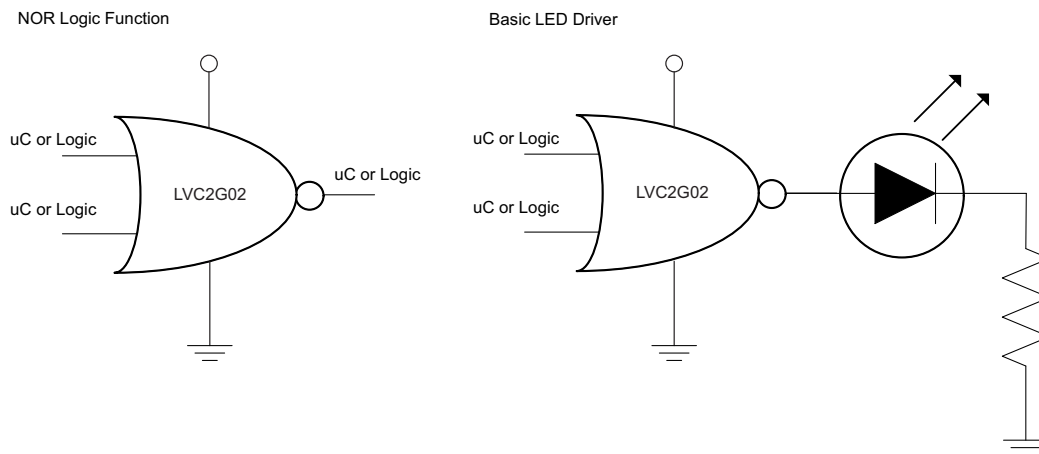
INPUTS		OUTPUT Y
A	B	
H	X	L
X	H	L
L	L	H

9 Application and Implementation

9.1 Application Information

The SN74LVC2G02 is a high-drive CMOS device that can be used for implement NOR logic with a high output drive, such as an LED application. It can produce 24-mA of drive current at 3.3 V making it Ideal for driving multiple outputs and good for high speed applications up to 100 Mhz. The inputs are 5.5-V tolerant allowing translation down to V_{CC} .

9.2 Typical Application



9.2.1 Design Requirements

This device uses CMOS technology and has balanced output drive. Care should be taken to avoid bus contention because it can drive currents that would exceed maximum limits. The high drive will also create fast edges into light loads, so routing and load conditions should be considered to prevent ringing.

9.2.2 Detailed Design Procedure

1. Recommended Input Conditions:
 - Rise time and fall time specs. See $(\Delta t/\Delta V)$ in the [Recommended Operating Conditions](#) table.
 - Specified high and low levels. See $(V_{IH}$ and $V_{IL})$ in the [Recommended Operating Conditions](#) table.
 - Inputs are overvoltage tolerant allowing them to go as high as $(V_I \text{ max})$ in the [Recommended Operating Conditions](#) table at any valid V_{CC} .
2. Recommend Output Conditions:
 - Load currents should not exceed $(I_O \text{ max})$ per output and should not exceed total current (continuous current through V_{CC} or GND) for the part. These limits are located in the [Absolute Maximum Ratings](#) table.
 - Outputs should not be pulled above V_{CC} .

Typical Application (continued)

9.2.3 Application Curves

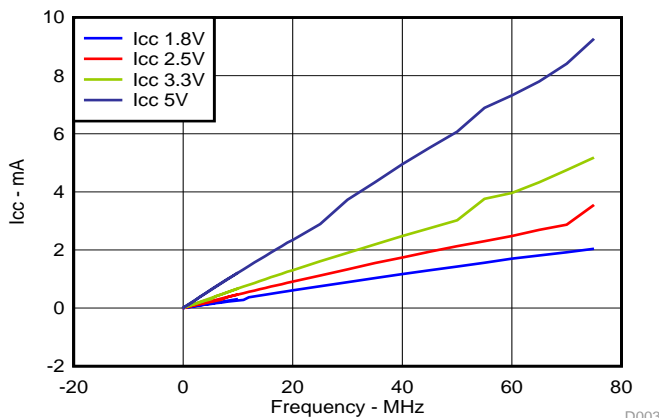


Figure 4. I_{CC} vs Frequency

10 Power Supply Recommendations

The power supply can be any voltage between the min and max supply voltage rating located in the [Recommended Operating Conditions](#) table.

Each VCC pin should have a good bypass capacitor to prevent power disturbance. For devices with a single supply, a 0.1- μ F capacitor is recommended. If there are multiple VCC pins, then a 0.01- μ F or 0.022- μ F capacitor is recommended for each power pin. It is ok to parallel multiple bypass capacitors to reject different frequencies of noise. A 0.1- μ F and 1- μ F capacitors are commonly used in parallel. The bypass capacitor should be installed as close to the power pin as possible for best results.

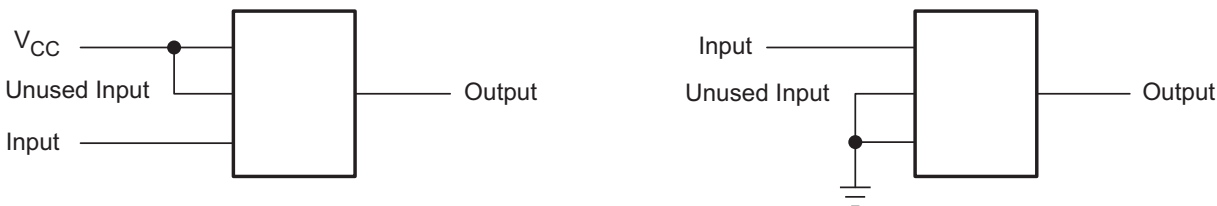
11 Layout

11.1 Layout Guidelines

When using multiple bit logic devices inputs should not ever float.

In many cases, functions or parts of functions of digital logic devices are unused; for example, when only two inputs of a triple-input AND gate are used or only 3 of the 4 buffer gates are used. Such input pins should not be left unconnected because the undefined voltages at the outside connections result in undefined operational states. Specified below are the rules that must be observed under all circumstances. All unused inputs of digital logic devices must be connected to a high or low bias to prevent them from floating. The logic level that should be applied to any particular unused input depends on the function of the device. Generally they will be tied to GND or VCC, whichever makes more sense or is more convenient.

11.2 Layout Example



12 デバイスおよびドキュメントのサポート

12.1 コミュニティ・リソース

The following links connect to TI community resources. Linked contents are provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's [Terms of Use](#).

TI E2E™ Online Community *TI's Engineer-to-Engineer (E2E) Community*. Created to foster collaboration among engineers. At e2e.ti.com, you can ask questions, share knowledge, explore ideas and help solve problems with fellow engineers.

Design Support *TI's Design Support* Quickly find helpful E2E forums along with design support tools and contact information for technical support.

12.2 商標

NanoFree, E2E are trademarks of Texas Instruments.

12.3 静電気放電に関する注意事項



すべての集積回路は、適切なESD保護方法を用いて、取扱いと保存を行うようにして下さい。

静電気放電はわずかな性能の低下から完全なデバイスの故障に至るまで、様々な損傷を与えます。高精度の集積回路は、損傷に対して敏感であり、極めてわずかなパラメータの変化により、デバイスに規定された仕様に適合しなくなる場合があります。

12.4 Glossary

[SLYZ022](#) — *TI Glossary*.

This glossary lists and explains terms, acronyms, and definitions.

13 メカニカル、パッケージ、および注文情報

以降のページには、メカニカル、パッケージ、および注文に関する情報が記載されています。この情報は、そのデバイスについて利用可能な最新のデータです。このデータは予告なく変更されることがあり、ドキュメントが改訂される場合もあります。本データシートのブラウザ版を使用されている場合は、画面左側の説明をご覧ください。

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
SN74LVC2G02DCTR	ACTIVE	SSOP	DCT	8	3000	RoHS & Green	NIPDAU SN	Level-1-260C-UNLIM	-40 to 125	(2WI5, C02) (R, Z)	Samples
SN74LVC2G02DCTRE4	ACTIVE	SSOP	DCT	8	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	C02 (R, Z)	Samples
SN74LVC2G02DCUR	ACTIVE	VSSOP	DCU	8	3000	RoHS & Green	NIPDAU SN	Level-1-260C-UNLIM	-40 to 125	(C02J, C02Q, C02R)	Samples
SN74LVC2G02DCUT	ACTIVE	VSSOP	DCU	8	250	RoHS & Green	NIPDAU SN	Level-1-260C-UNLIM	-40 to 125	(C02J, C02Q, C02R)	Samples
SN74LVC2G02YZPR	ACTIVE	DSBGA	YZP	8	3000	RoHS & Green	SNAGCU	Level-1-260C-UNLIM	-40 to 125	CBN	Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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OTHER QUALIFIED VERSIONS OF SN74LVC2G02 :

- Enhanced Product : [SN74LVC2G02-EP](#)

NOTE: Qualified Version Definitions:

- Enhanced Product - Supports Defense, Aerospace and Medical Applications

TAPE AND REEL INFORMATION

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE


*All dimensions are nominal

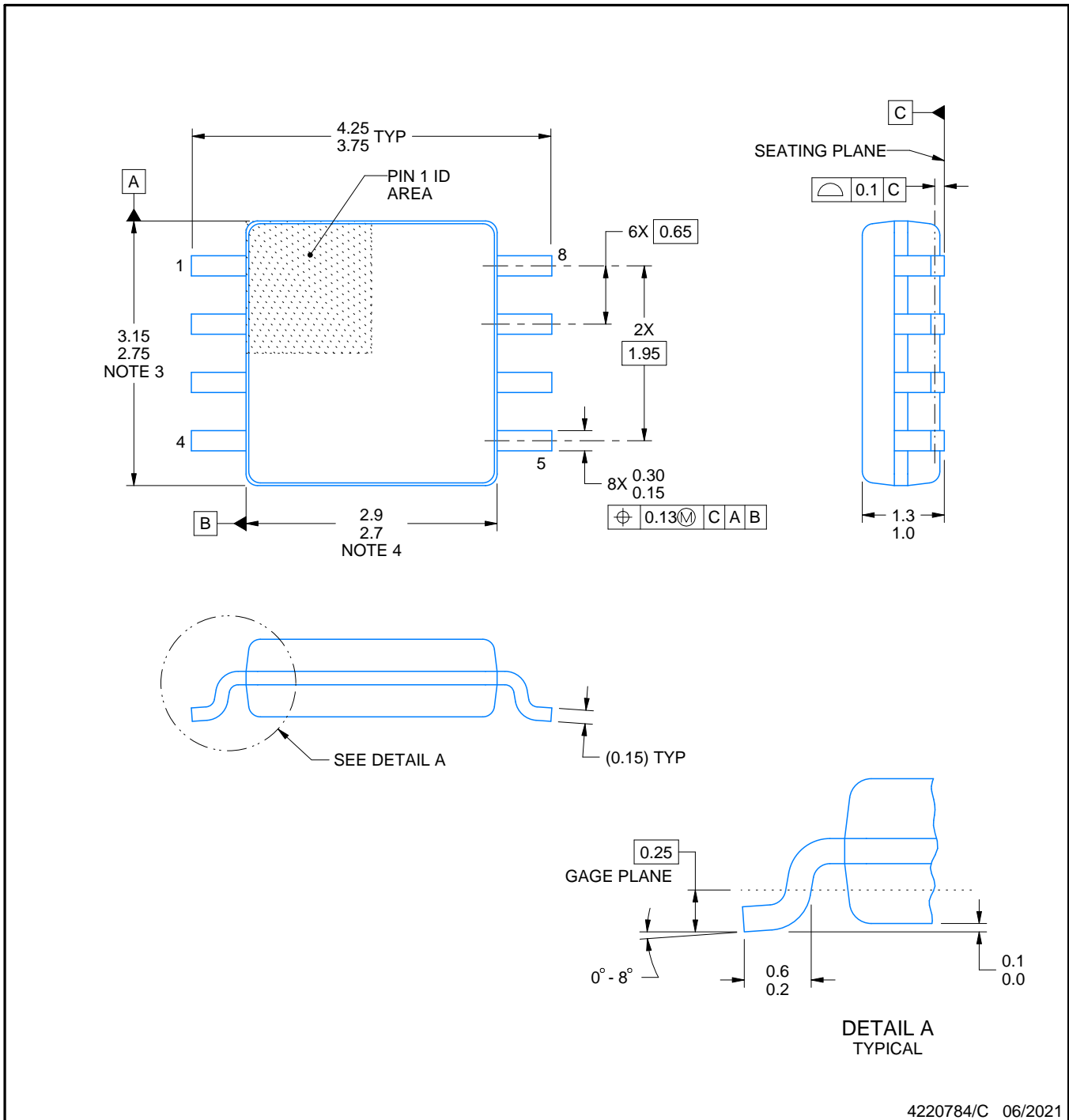
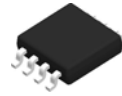
Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
SN74LVC2G02DCTR	SSOP	DCT	8	3000	180.0	12.4	3.15	4.35	1.55	4.0	12.0	Q3
SN74LVC2G02DCTRE4	SSOP	DCT	8	3000	177.8	12.4	3.45	4.4	1.45	4.0	12.0	Q3
SN74LVC2G02DCUR	VSSOP	DCU	8	3000	178.0	9.0	2.25	3.35	1.05	4.0	8.0	Q3
SN74LVC2G02DCUT	VSSOP	DCU	8	250	178.0	9.5	2.25	3.35	1.05	4.0	8.0	Q3
SN74LVC2G02DCUT	VSSOP	DCU	8	250	178.0	9.0	2.25	3.35	1.05	4.0	8.0	Q3
SN74LVC2G02YZPR	DSBGA	YZP	8	3000	178.0	9.2	1.02	2.02	0.63	4.0	8.0	Q1

TAPE AND REEL BOX DIMENSIONS



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
SN74LVC2G02DCTR	SSOP	DCT	8	3000	190.0	190.0	30.0
SN74LVC2G02DCTRE4	SSOP	DCT	8	3000	183.0	183.0	20.0
SN74LVC2G02DCUR	VSSOP	DCU	8	3000	180.0	180.0	18.0
SN74LVC2G02DCUT	VSSOP	DCU	8	250	202.0	201.0	28.0
SN74LVC2G02DCUT	VSSOP	DCU	8	250	180.0	180.0	18.0
SN74LVC2G02YZPR	DSBGA	YZP	8	3000	220.0	220.0	35.0



4220784/C 06/2021

NOTES:

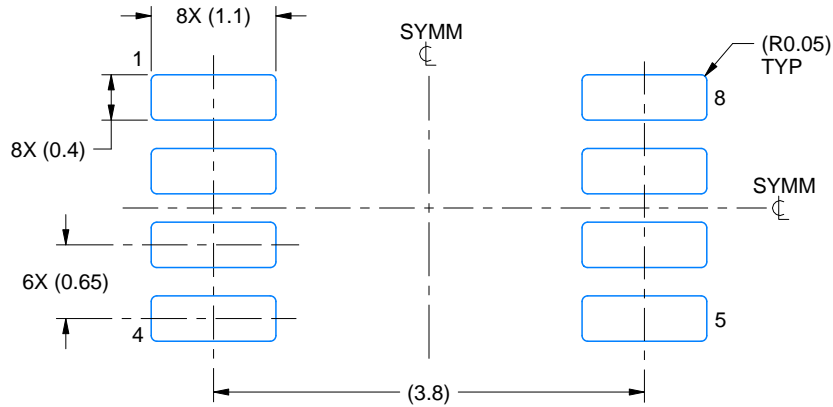
1. All linear dimensions are in millimeters. Dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 mm per side.
4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.

EXAMPLE BOARD LAYOUT

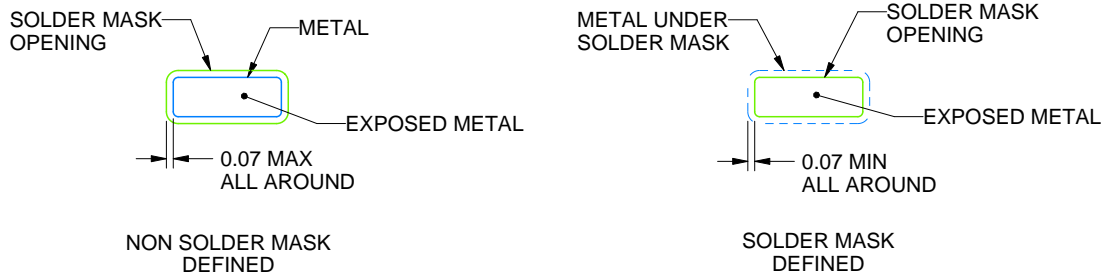
DCT0008A

SSOP - 1.3 mm max height

SMALL OUTLINE PACKAGE



LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE:15X



SOLDER MASK DETAILS

4220784/C 06/2021

NOTES: (continued)

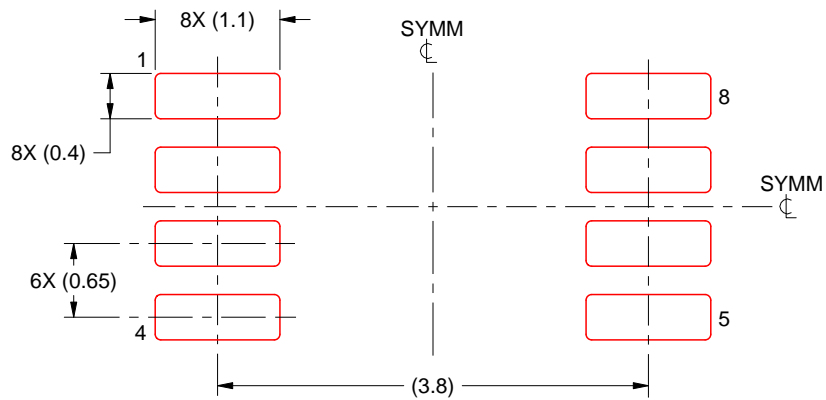
- 5. Publication IPC-7351 may have alternate designs.
- 6. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

EXAMPLE STENCIL DESIGN

DCT0008A

SSOP - 1.3 mm max height

SMALL OUTLINE PACKAGE



SOLDER PASTE EXAMPLE
BASED ON 0.125 mm THICK STENCIL
SCALE:15X

4220784/C 06/2021

NOTES: (continued)

7. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
8. Board assembly site may have different recommendations for stencil design.

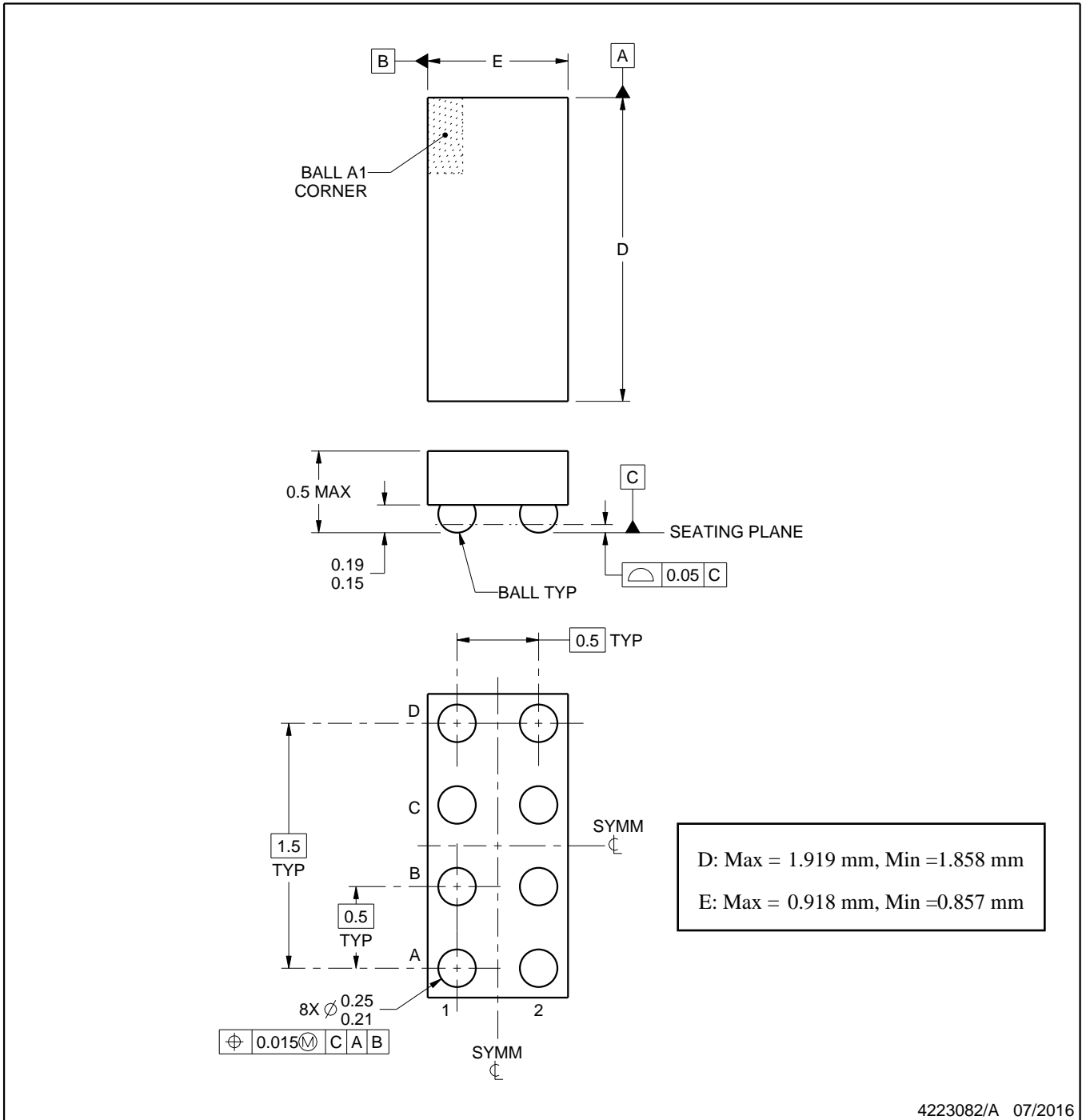
YZP0008



PACKAGE OUTLINE

DSBGA - 0.5 mm max height

DIE SIZE BALL GRID ARRAY



NOTES:

1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.

EXAMPLE BOARD LAYOUT

YZP0008

DSBGA - 0.5 mm max height

DIE SIZE BALL GRID ARRAY



LAND PATTERN EXAMPLE
SCALE:40X



SOLDER MASK DETAILS
NOT TO SCALE

4223082/A 07/2016

NOTES: (continued)

3. Final dimensions may vary due to manufacturing tolerance considerations and also routing constraints. For more information, see Texas Instruments literature number SNVA009 (www.ti.com/lit/snva009).

EXAMPLE STENCIL DESIGN

YZP0008

DSBGA - 0.5 mm max height

DIE SIZE BALL GRID ARRAY



SOLDER PASTE EXAMPLE
BASED ON 0.1 mm THICK STENCIL
SCALE:40X

4223082/A 07/2016

NOTES: (continued)

4. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release.

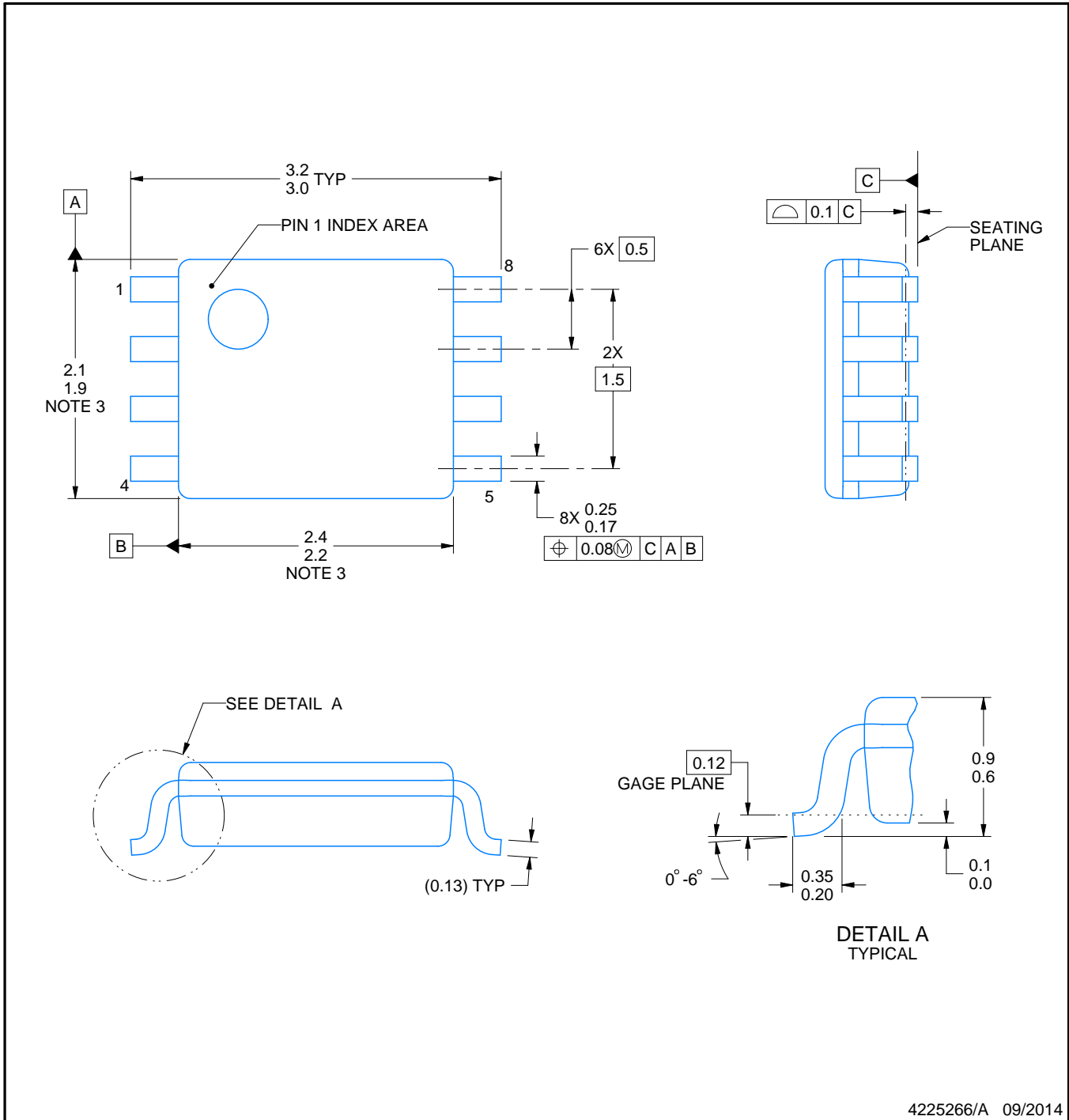
DCU0008A



PACKAGE OUTLINE

VSSOP - 0.9 mm max height

SMALL OUTLINE PACKAGE



4225266/A 09/2014

NOTES:

- All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
- This drawing is subject to change without notice.
- This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 mm per side.
- Reference JEDEC registration MO-187 variation CA.

EXAMPLE BOARD LAYOUT

DCU0008A

VSSOP - 0.9 mm max height

SMALL OUTLINE PACKAGE



LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE: 25X



4225266/A 09/2014

NOTES: (continued)

- 5. Publication IPC-7351 may have alternate designs.
- 6. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

EXAMPLE STENCIL DESIGN

DCU0008A

VSSOP - 0.9 mm max height

SMALL OUTLINE PACKAGE



SOLDER PASTE EXAMPLE
BASED ON 0.125 mm THICK STENCIL
SCALE: 25X

4225266/A 09/2014

NOTES: (continued)

7. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
8. Board assembly site may have different recommendations for stencil design.

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